AMENDMENTS TO THE CLAIMS:

Please cancel claims 13, 15-18 and 23-25 without prejudice or disclaimer.

1-13. (Canceled)

14. (Previously presented) A method for producing a transparent laminate comprising:

preparing a transparent substrate;

depositing a high-refractive-index transparent thin film by a vacuum dry process;

depositing a silver transparent conductive thin film by a vacuum dry process;

repeating forming of the high-refractive-index transparent thin film and the silver transparent conductive thin film at least three times to thereby form at least three combination thin-film layers of the high-refractive-index transparent thin film and the silver transparent conductive thin film successively laminated on a surface of said transparent substrate; and

depositing another high-refractive-index transparent thin film on a surface of said combination thin-film layer by the vacuum dry process,

wherein, when said silver transparent conductive thin films are deposited by the vacuum dry process, a temperature T (K) of said transparent substrate at the time of the deposition of said films is set to be in a range $340 \leq T \leq 390$, and a deposition rate R (nm/sec) of said silver transparent conductive thin films is set to be $R = (1/40)x(T-300)\pm 0.5$.

15-18. (Canceled)

19. (Previously presented) The method of claim 14, further comprising depositing a low-refractive-index transparent thin film.

20. (Previously presented) The method of claim 19, wherein the low-refractive-index transparent thin film is deposited before any high-refractive-index thin film is deposited.

21. (Previously presented) The method of claim 19, wherein the low-refractive-index transparent thin film is deposited after all of the high-refractive-index thin films are deposited.

22. (Previously presented) The method of claim 14, further comprising disposing said transparent laminate in front of a display portion of a plasma display panel.

23-25. (Canceled)

26. (Previously presented) The method of claim 14, wherein said vacuum dry process comprises a sputtering process.

27. (Previously presented) The method of claim 14, wherein said silver transparent conductive thin film comprises silver and 5 % by weight of gold.

28. (Currently amended) The method of claim 14, wherein said repeated depositing is repeated ~~only~~ three times to form three combination thin-film layers.

29. (Currently amended) The method of claim 14 ~~13~~, wherein said silver transparent conductive thin films comprise a thickness in range from 5 nm to 20 nm.

30. (Currently amended) The method of claim 14 ~~13~~, wherein said high-refractive-index transparent thin film which is formed on said transparent substrate and said another high-refractive-index transparent thin film comprise a thickness in a range from 20 nm to 50 nm.

31. (Currently amended) The method of claim 14 ~~13~~, wherein said high-refractive-index transparent thin films other than said high-refractive-index transparent thin film which is formed on said transparent substrate and said another high-refractive-index transparent thin film, comprise a thickness in a range from 40 nm to 100 nm.

32. (Currently amended) A method for producing a transparent laminate comprising:

depositing a high-refractive-index transparent thin film on a transparent substrate by a vacuum dry process;

depositing a silver transparent conductive thin film on said high-refractive-index transparent thin film by a vacuum dry process;

repeating the depositing of the high-refractive-index transparent thin film and the silver transparent conductive thin film at least three times to thereby form at least three combination thin-film layers of the high-refractive-index transparent thin film and the silver transparent conductive thin film successively laminated on said transparent substrate; and

depositing another high-refractive-index transparent thin film on said combination thin-film layers by a vacuum dry process,

wherein at the time of the deposition of said silver transparent conductive thin films, a temperature T (K) of said transparent substrate is set to be in a range $340 \leq T \leq 390$ ~~410~~, and a

deposition rate R (nm/sec) of said silver transparent conductive thin films is set to be R = (1/40)x(T-300).